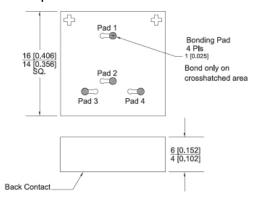
# MBD3047-C18 Planar Tunnel Diode

## C18 Chip Outline



Dimensions in mils [mm] mils (mm)

#### Chip assembly

The alloyed junction of the germanium planar diode (or back diode), is sensitive to mechanical pressure and high temperatures. Thus it must be handled as follows (as an example).

Die attach: Epoxy only: less than +125° C cure temperature recommended. Wire bond: +160° C base +160° C capillary temperature, presssure < 20 grams. A wedge bond is done on an offset bonding pad. Bonding should not be done directly over the junction. Bond wire angle should leave small end of pad visually clear to assure junction is not bonded over.

### **Technical Characteristics**

#### **Product Features**

Rugged Germanium Planar Construction

**Excellent Temperature Stability** 

No DC Bias Required

Wide Video Bandwidth

MIL-STD-190500 & 883 Qualified

#### **Product Description**

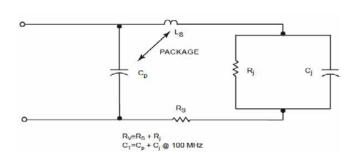
EclipseMDI MBD3047-C18, is a zero-bias, rugged Planar Tunnel Diode constructed with Germanium Planar. This tunnel diode exhibits excellent temperature stability, wide video bandwidth and is MIL STD-190500 & MIL-STD-883C qualified. The MBD3047-C18 is available in chip form.

#### **Maximum Ratings**

Storage Temperature	65° to +125°C
Operating Temperature	65° to +110°C
Input Power Handling	+17dBm CW
or 3 ERG spike	
Soldering Temperature	+160° C

	Specifications				
Parameters	Conditions	MIN	Typical	MAX	UNITS
lp		300		350	μΑ
Cj	Vr=Vv, f=100MHz			.30	pF
K[Y]	Pin=-20dBm		550		mV/mW
Rv	R)Load)=10K, f=10GHz		110		Ω Ohms
lp/lv		2.5			
Vr	If=500μA		400		mV
Vf	If=3mA			125	mV

#### Diode equivalent circuit



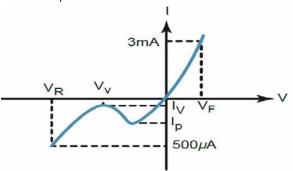


## About EclipseMDI

ECLIPSE Microdevices is located in San Jose, California. ECLIPSE has been developing high performance analog semiconductors for use in wireless radio frequency (RF), microwave, and millimeter wave for commercial and industrial applications. ECLIPSE has formed a strategic alliances - with foundries that features leading state-of-the-art process technologies and with manufacturing facilities for high-volume production of innovative RFIC's.

Quality products that serve the industry. Today and tomorrow.

#### Back diode parameters



## **Product Export Classificiation**

ECCN: EAR 99 (unless otherwise specified) HTS: 8542330000





